Silicon PNP Power Transistors 2N3183

DESCRIPTION

- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For medium-speed switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

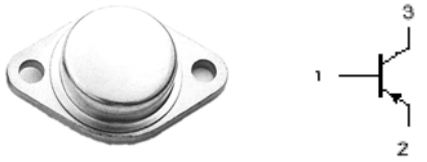

Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-40	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
P_C	Collector power dissipation	T_C=25℃	75	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{(th)\ jc}$	Thermal resistance junction to case	1.17	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEO}	Collector-emitter sustaining voltage	I_C=-0.2A ;I_B=0	-40			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=-5A; I_B=-1A			-1.5	V
$V_{BE(on)}$	Base-emitter on voltage	I_C=-5A ; V_{CE}=-4V			-2.0	V
I_{CEO}	Collector cut-off current	V_{CE}=Rated V_{CEO}; I_B=0			-5.0	mA
I_{CBO}	Collector cut-off current	V_{CB}=Rated V_{CBO}; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-1.0	mA
h_{FE-1}	DC current gain	I_C=-0.3A ; V_{CE}=-4V	30			
h_{FE-2}	DC current gain	I_C=-3A ; V_{CE}=-4V	15			

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PACKAGE OUTLINE

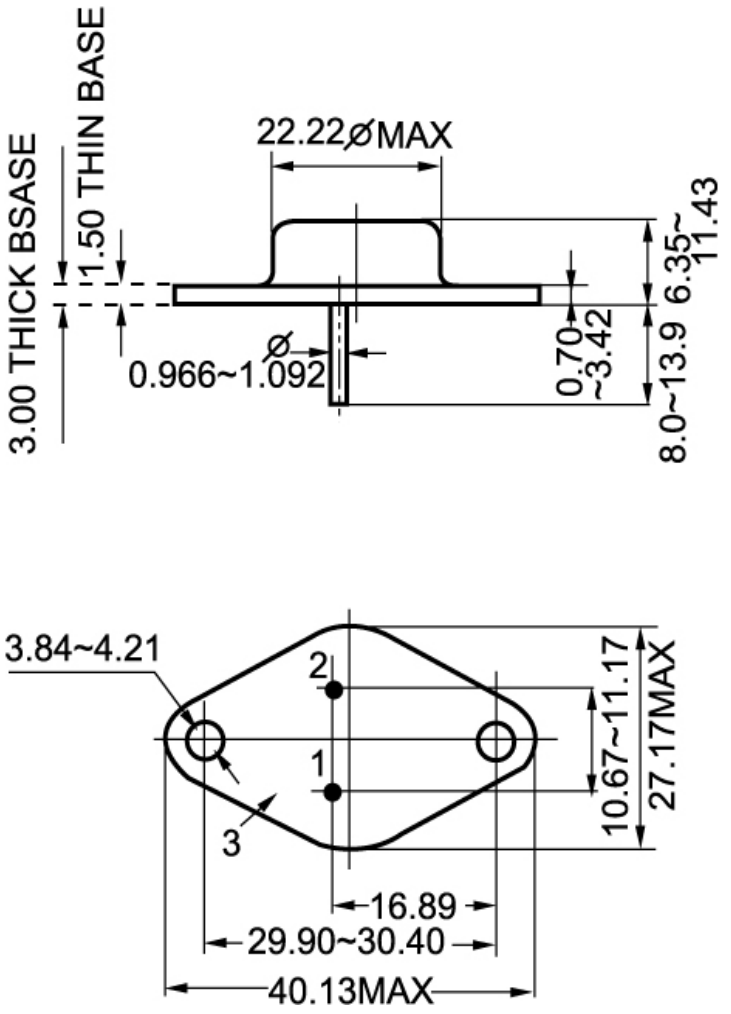

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)